



100V 115mΩ N-Ch Power MOSFET

Features

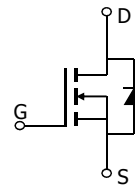
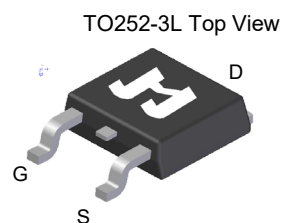
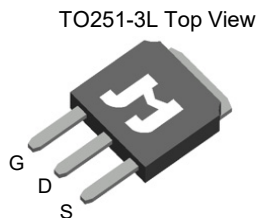
- Low Gate Charge
- High Current Capability
- 100% UIS Tested, 100% R_g Tested

Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems

Product Summary

Parameter	Typ.	Unit
V _{DS}	100	V
V _{GS(th)}	1.7	V
I _D (@ V _{GS} = 10V) ⁽¹⁾	6	A
R _{DS(ON)} (@ V _{GS} = 10V)	115	mΩ
R _{DS(ON)} (@ V _{GS} = 4.5V)	144	mΩ

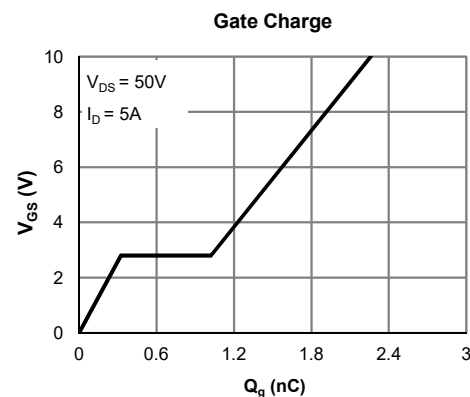
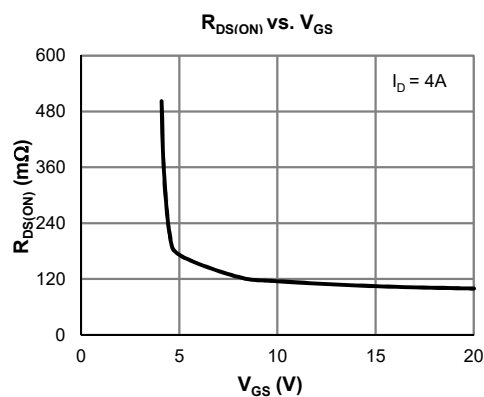


Ordering Information

Device	Package	# of Pins	Marking	MSL	T _J (°C)	Media	Quantity (pcs)
JMSL10130AH-U	TO251-3L	3	SL10130A	N/A	-55 to 150	Tube	80
JMSL10130AK-13	TO252-3L	3	SL10130A	3	-55 to 150	13-inch Reel	2500

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DS}	100	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I _D	T _C = 25°C	6
		T _C = 100°C	4
Pulsed Drain Current ⁽²⁾	I _{DM}	10	A
Avalanche Current ⁽³⁾	I _{AS}	1.8	A
Avalanche Energy ⁽³⁾	E _{AS}	4.9	mJ
Power Dissipation ⁽⁴⁾	P _D	T _C = 25°C	17
		T _C = 100°C	7
Junction & Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C





Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	1.7	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 4\text{A}$		115	138	$\text{m}\Omega$
	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 3\text{A}$		144	180	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 4\text{A}$		5.8		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.7	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			17	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		96		pF
Output Capacitance	C_{oss}			32		pF
Reverse Transfer Capacitance	C_{rss}			3.6		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.9		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 5\text{A}$		2.3		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			1.3		nC
Gate Source Charge	Q_{gs}			0.3		nC
Gate Drain Charge	Q_{gd}			0.7		nC
Turn-On Delay Time	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 10\Omega, R_{GEN} = 6\Omega$		2.1		ns
Turn-On Rise Time	t_r			3.3		ns
Turn-Off Delay Time	$t_{D(off)}$			7.2		ns
Turn-Off Fall Time	t_f			3.2		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 5\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		25	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 5\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		15		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	48	58	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.0	7.5	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 3\text{mH}, V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

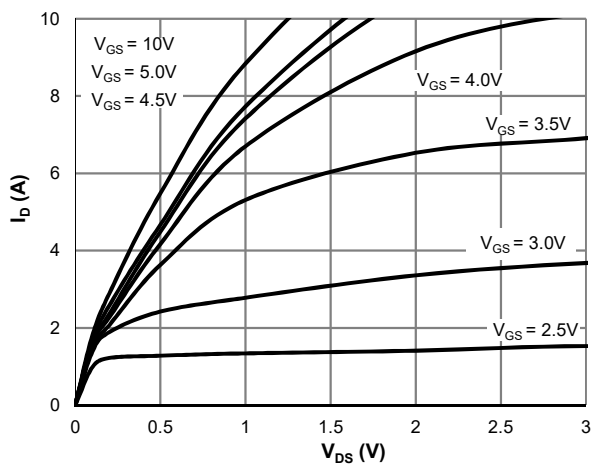


Figure 1: Saturation Characteristics

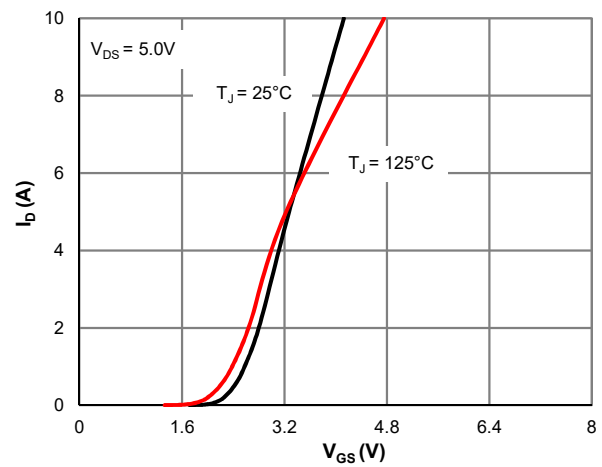


Figure 2: Transfer Characteristics

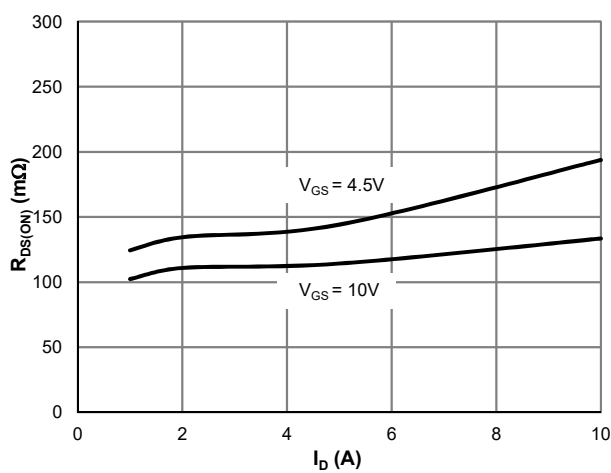


Figure 3: $R_{DS(ON)}$ vs. Drain Current

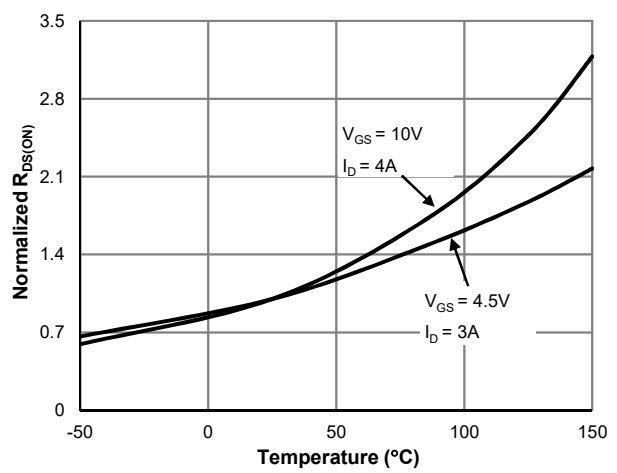


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

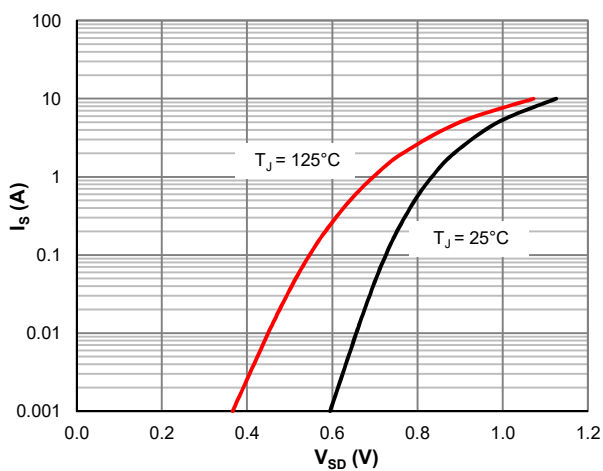


Figure 5: Body-Diode Characteristics

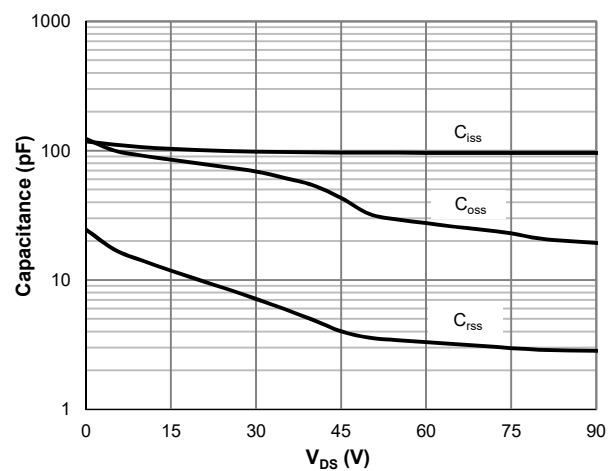


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

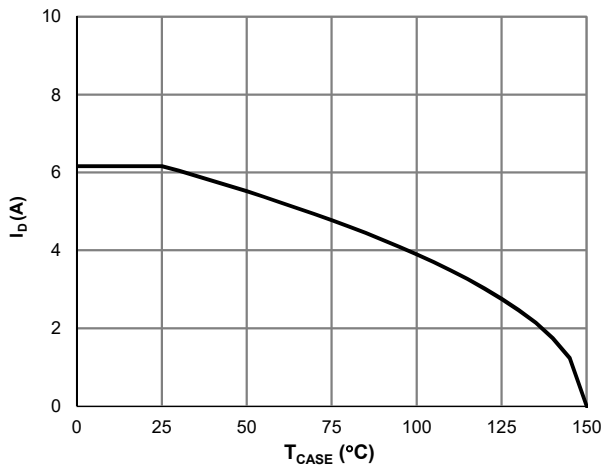


Figure 7: Current De-rating

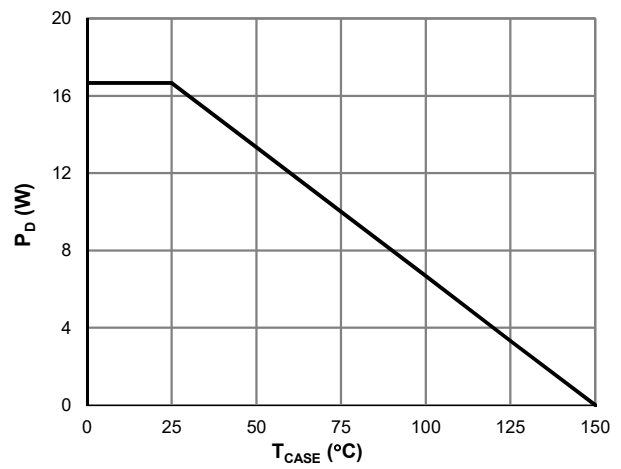


Figure 8: Power De-rating

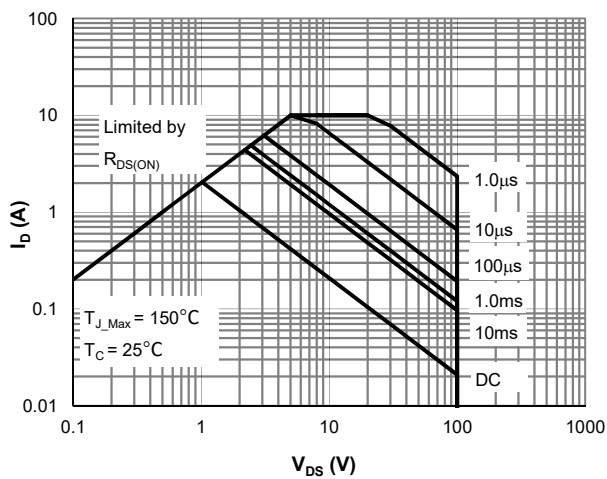


Figure 9: Maximum Safe Operating Area

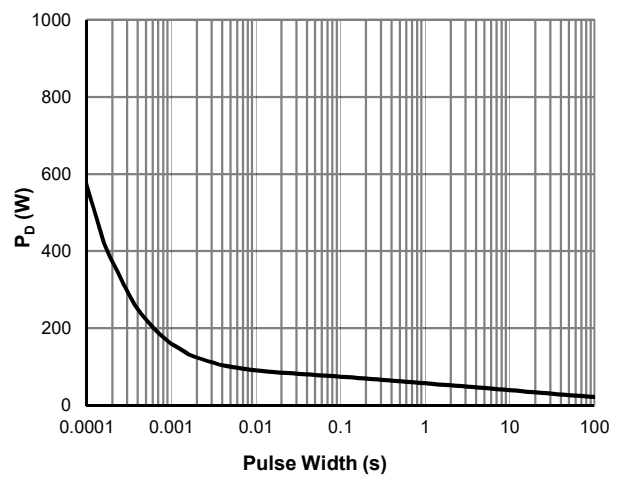


Figure 10: Single Pulse Power Rating, Junction-to-Case

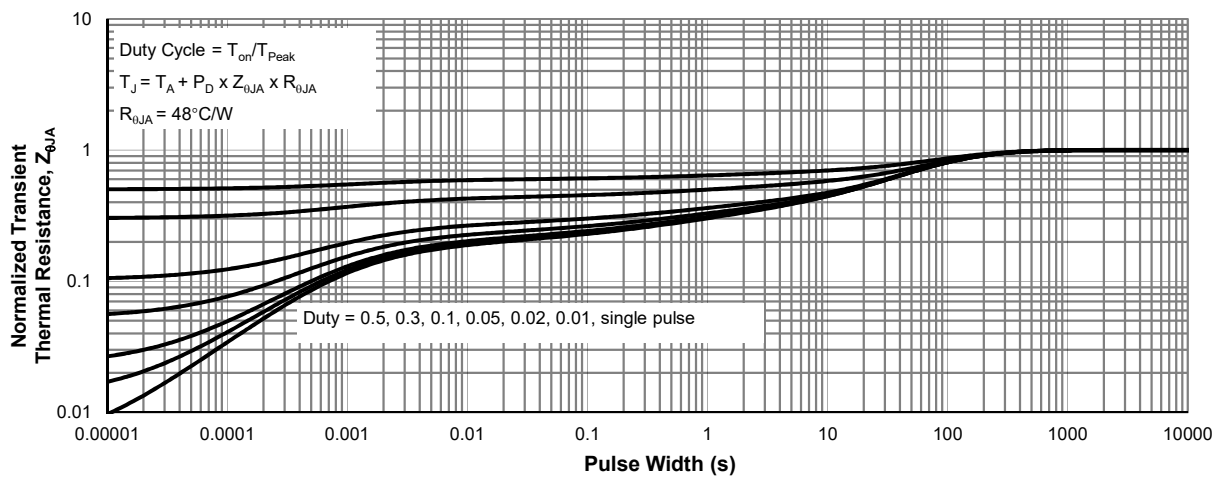
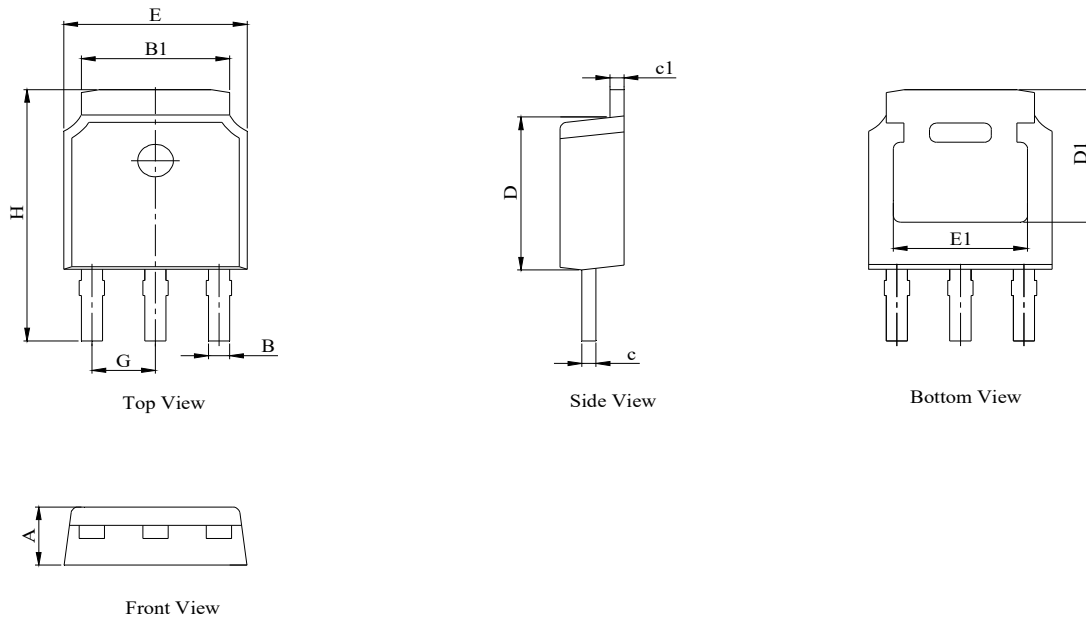


Figure 11: Normalized Maximum Transient Thermal Impedance

TO251-3L Package Information

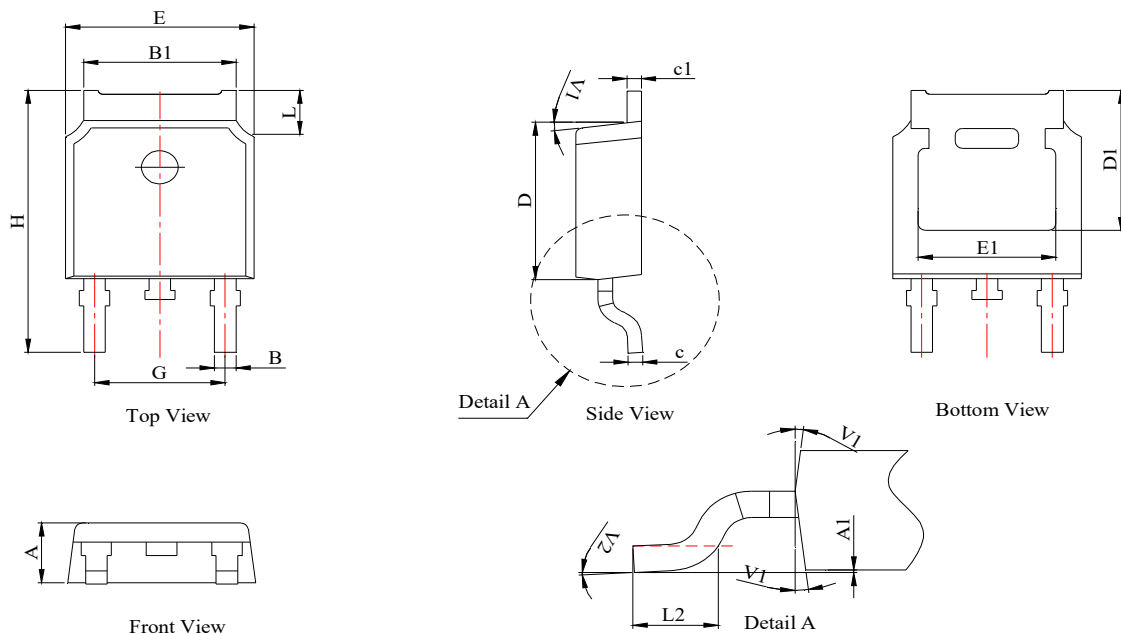
Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.10		2.50
B	0.66		0.86
B1	5.15		5.48
c	0.44		0.58
c1	0.44		0.58
D	5.90		6.30
D1	5.30 REF		
E	6.40		6.80
E1	4.83 REF		
G	2.19	2.29	2.39
H	10.60		11.80

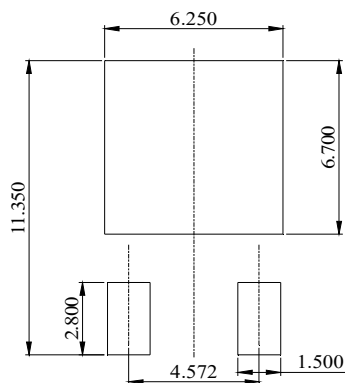
TO252-3L Package Information

Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.10		2.50
A1	0	-	0.10
B	0.66		0.86
B1	5.18		5.48
c	0.40		0.60
c1	0.44		0.58
D	5.90		6.30
D1	5.30REF		
E	6.40		6.80
E1	4.63		
G	4.47		4.67
H	9.50		10.70
L	1.09		1.21
L2	1.35		1.65
V1		7°	
V2	0°	-	6°

Recommended Footprint



DIMENSIONS: MILLIMETERS

单击下面可查看定价，库存，交付和生命周期等信息

[>>JW\(捷捷微\)](#)